Silicon Epitaxial Planar Diode for High Speed Switching

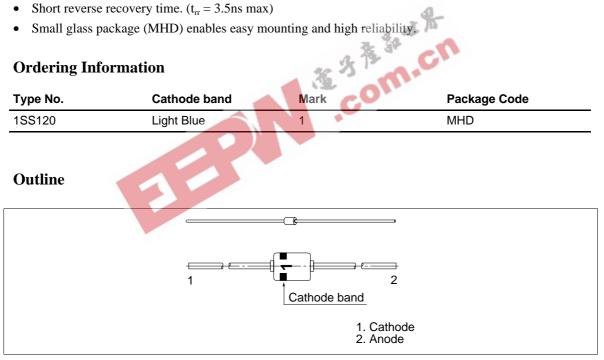
# **HITACHI**

ADE-208-167B (Z) Rev. 2 Aug. 1995

### **Features**

- Low capacitance. (C = 3.0 pF max) •
- Short reverse recovery time. ( $t_{rr} = 3.5$ ns max) •
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## **Ordering Information**





## **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

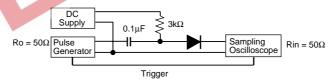
Item	Symbol	Value	Unit
Peak reverse voltage	V <sub>RM</sub>	70	V
Reverse voltage	V <sub>R</sub>	60	V
Peak forward current	I <sub>FM</sub>	450	mA
Non-Repetitive peak forward surge current	l <sub>FSM</sub> *	1	А
Average forward current	I <sub>o</sub>	150	mA
Power dissipation	Pd	250	mW
Junction temperature	Тј	175	°C
Storage temperature	Tstg	-65 to +175	°C

Note: Within 1s forward surge current.

# **Electrical Characteristics** (Ta = 25°C)

Note: Within 1s forward surge current.							
Electrical Characteristics (Ta = 25°C)							
Symbol	Min	Тур	Max	Unit	Test Condition		
V <sub>F</sub>	-	<b>F</b>	0.8	V	$I_F = 10 \text{mA}$		
I <sub>R</sub>	-7	+	0.1	μA	$V_R = 60V$		
С		A	3.0	pF	$V_R = 1V$ , f = 1MHz		
t"*	-	_	3.5	ns	$I_{\scriptscriptstyle F}=10mA,V_{\scriptscriptstyle R}=6V,R_{\scriptscriptstyle L}=50\Omega$		
	Symbol V <sub>F</sub> I <sub>R</sub> C	Symbol  Min    V <sub>F</sub> —    I <sub>R</sub> —    C  —	Symbol  Min  Typ    V <sub>F</sub> I <sub>R</sub> C	Symbol  Min  Typ  Max $V_F$ -  -  0.8 $I_R$ -  -  0.1    C  -  -  3.0	Symbol  Min  Typ  Max  Unit $V_F$ 0.8  V $I_R$ 0.1 $\mu A$ C    3.0  pF		

Note: Reverse recovery time test circuit



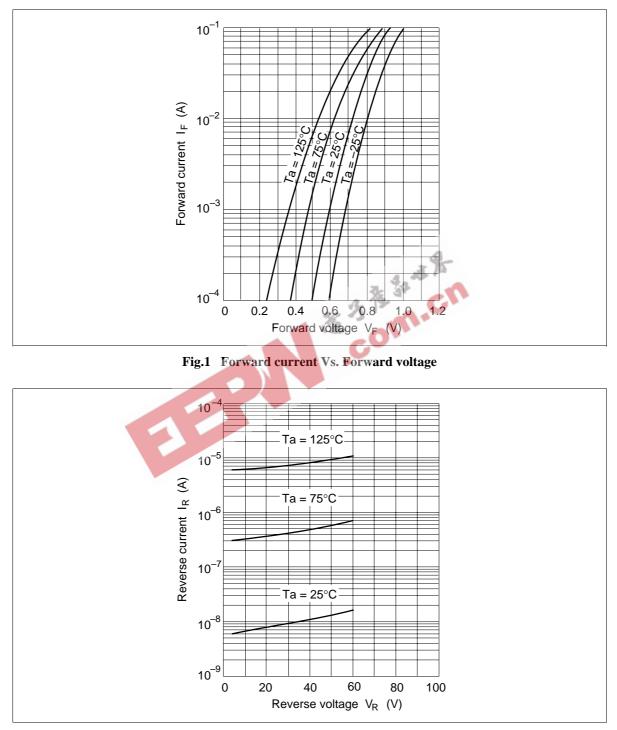
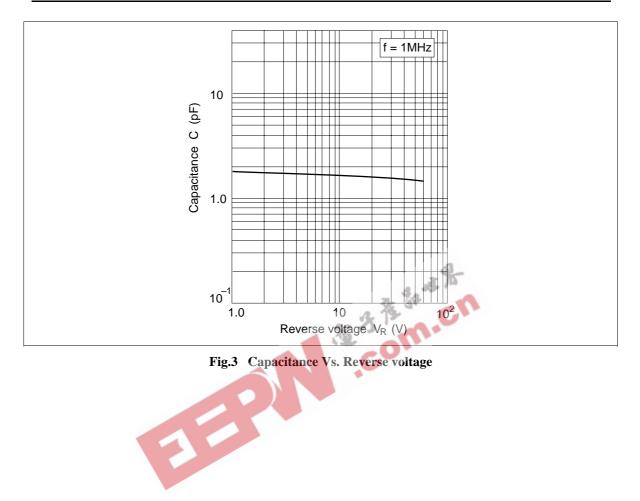
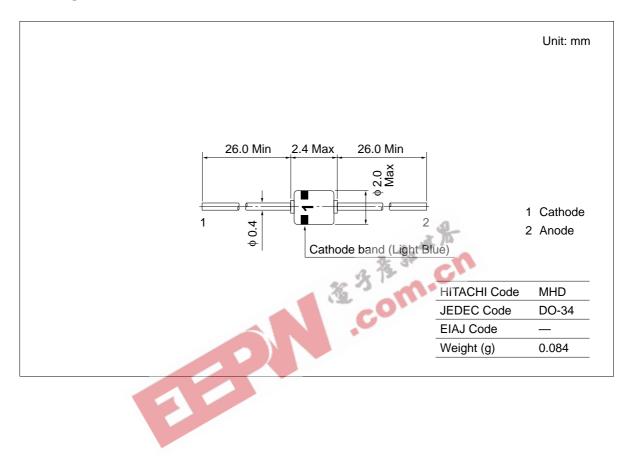


Fig.2 Reverse current Vs. Reverse voltage

## HITACHI



## **Package Dimensions**



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